

700V N-Channel MOSFET

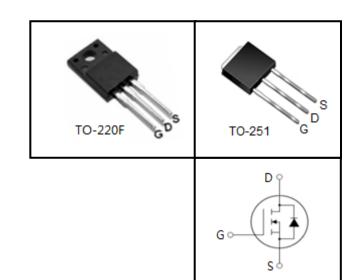
FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Package	Marking		
CS7N70F	TO-220F	CS7N70F		
CS7N70U	TO-251	CS7N70U		



Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted					
Parameter	Symbol -	Va	Unit		
raiametei		TO-220F	TO-251	Onit	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	700		V	
Continuous Drain Current	I _D	7		А	
Pulsed Drain Current (note1)	I _{DM}	28		А	
Gate-Source Voltage	V_{GSS}	±30		V	
Single Pulse Avalanche Energy (note2)	E _{AS}	218		mJ	
Avalanche Current (note1)	I _{AS}	6.6		А	
Repetitive Avalanche Energy (note1)	E _{AR}	130		mJ	
Power Dissipation (T _C = 25°C)	P_{D}	64	83	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~	+150	°C	

Thermal Resistance				
Bernander	Symbol	Va	l locit	
Parameter		TO-220F	TO-251	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	1.95	1.5	00/14/
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60	°C/W



Specifications $T_J = 25^{\circ}$ C, unless otherwise noted						
Parameter	Symbol	Tool Conditions	Value			11
		Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	700			V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 700 \text{V}, V_{GS} = 0 \text{V}, T_{J} = 25^{\circ}\text{C}$			1	μΑ
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	٧
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_D = 3.5A$		1.15	1.4	Ω
Dynamic						
Input Capacitance	C _{iss}	V - 0V		1010		pF
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0MHz$		100		
Reverse Transfer Capacitance	C_{rss}			15		
Total Gate Charge	Q_g	$V_{DD} = 560V, I_{D} = 7A,$ $V_{GS} = 10V$		35		nC
Gate-Source Charge	Q_{gs}			5		
Gate-Drain Charge	Q_{gd}	65		19		
Turn-on Delay Time	t _{d(on)}			40		
Turn-on Rise Time	t _r	V _{DD} = 350V, I _D =7A,		25		ns
Turn-off Delay Time	t _{d(off)}	$R_G = 25 \Omega$		152		
Turn-off Fall Time	t _f			39		
Drain-Source Body Diode Character	istics					
Continuous Body Diode Current	I _S	_			7	^
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			28	A
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}\text{C}, I_{SD} = 3.5\text{A}, V_{GS} = 0\text{V}$			1.4	V
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_{S} = 7A,$		580		ns
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /µs		1.87		μC

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}C$
- 3. Pulse Test: Pulse width ≤ 325µs, Duty Cycle ≤ 1%



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^{\circ}C$)

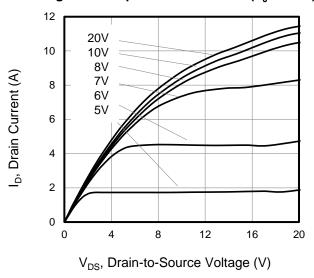


Figure 3. Drain Current vs. Temperature

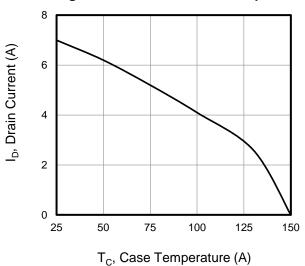


Figure 5. Transfer Characteristics

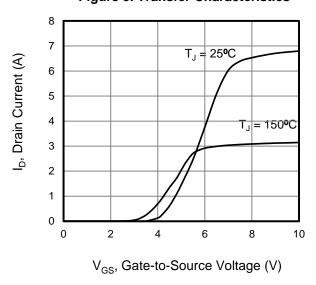
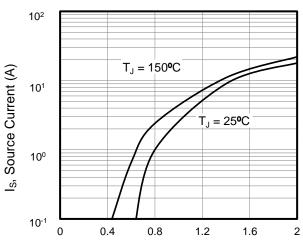


Figure 2. Body Diode Forward Voltage



V_{SD}, Source-to-Drain Voltage (V)

Figure 4. BV_{DSS} Variation vs. Temperature

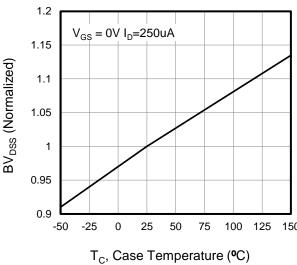
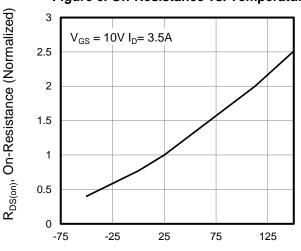


Figure 6. On-Resistance vs. Temperature



T_J, Junction Temperature (°C)



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

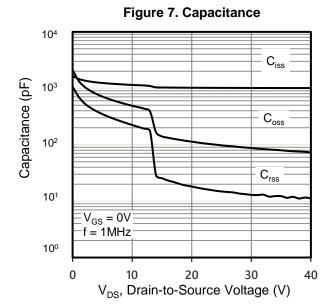


Figure 9. Transient Thermal Impedance TO-220F

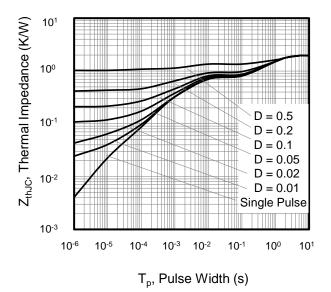


Figure 8. Gate Charge

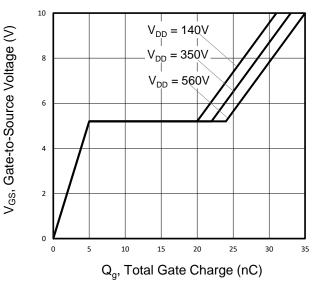


Figure 9. Transient Thermal Impedance TO-251

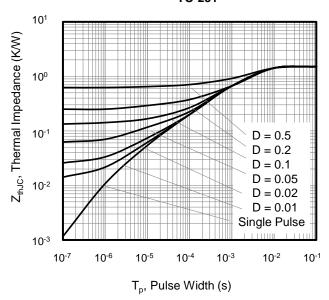




Figure A: Gate Charge Test Circuit and Waveform

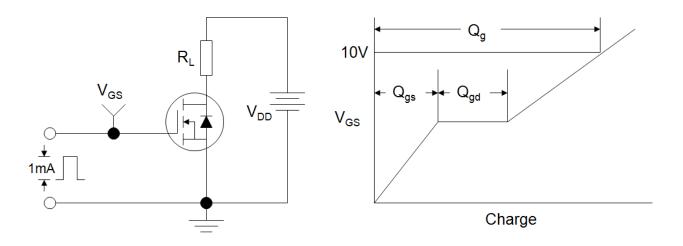


Figure B: Resistive Switching Test Circuit and Waveform

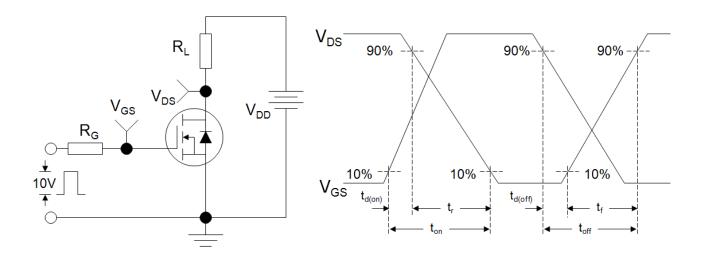
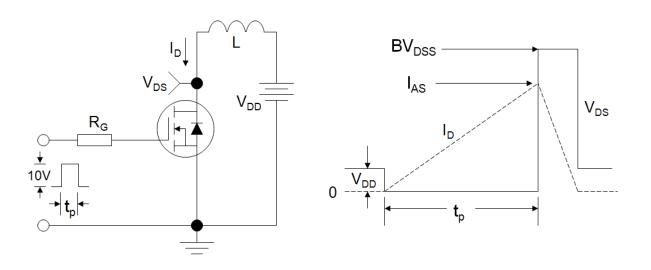
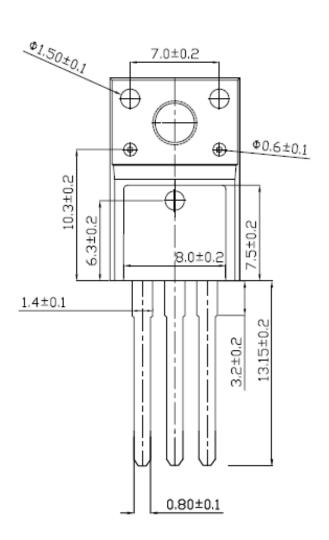


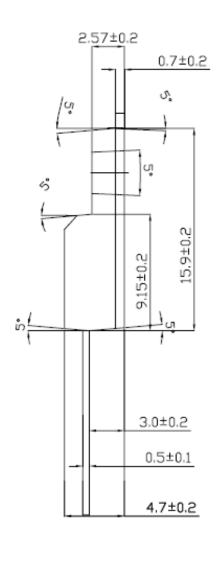
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





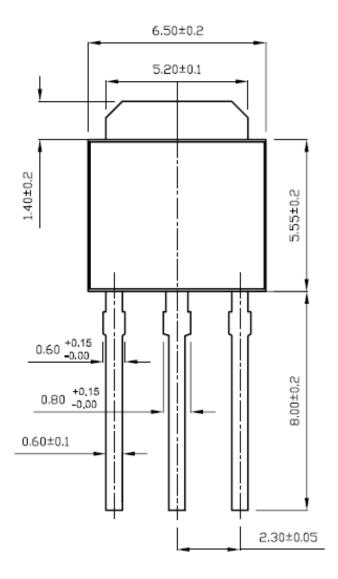
TO-220F

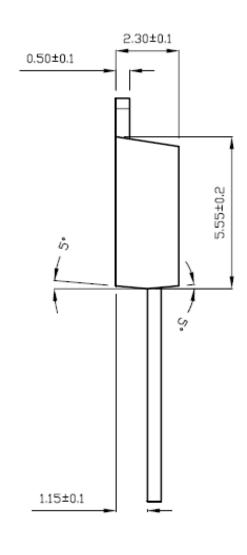






TO-251







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